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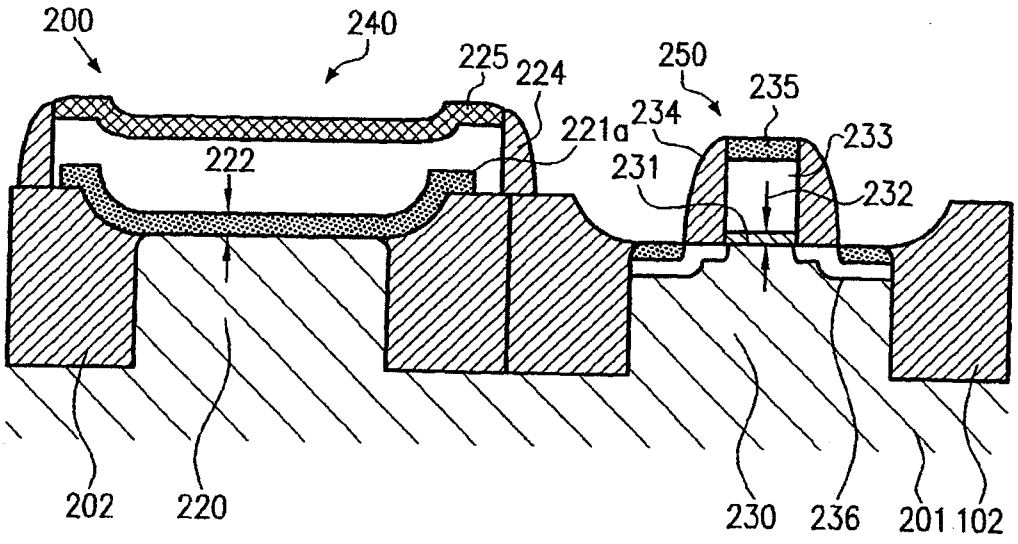
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(54) Title: SEMICONDUCTOR DEVICE INCLUDING A FIELD EFFECT TRANSISTOR AND A PASSIVE CAPACITOR HAVING REDUCED LEAKAGE CURRENT AND AN IMPROVED CAPACITANCE PER UNIT AREA



(57) Abstract: A semiconductor device comprises a field effect transistor (250) and a passive capacitor (240), wherein the dielectric layer (221a) of the capacitor (240) is comprised of a high-k material, whereas the gate insulation layer (231) of the field effect transistor (250) is formed of an ultra thin oxide layer or oxynitride layer so as to provide for superior carrier mobility at the interface between the gate insulation layer and the underlying channel region. Since carrier mobility in the capacitor is not of great importance, the high-k material allows the provision of high capacitance per unit area while featuring a thickness sufficient to effectively reduce leakage current.

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